

No. 2505

## 2SA1582/2SC4113

PNP/NPN Epitaxial Planar Silicon Transistors

### Switching Applications

(with Bias Resistance)

**Applications**

- Switching circuit, inverter circuit, interface circuit, driver circuit

**Features**

- On-chip bias resistance ( $R_1 = 2.2k\Omega, R_2 = \infty$ )
- Small-sized package (SPA)

( ): 2SA1582

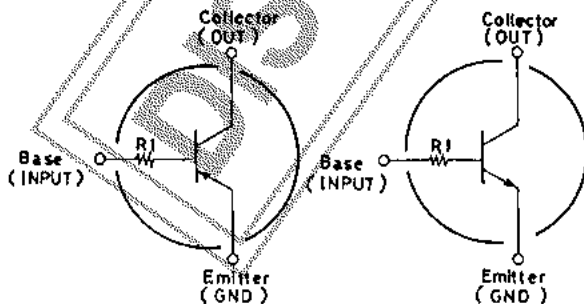
**Absolute Maximum Ratings at  $T_a = 25^\circ C$**

			unit
Collector to Base Voltage	$V_{CBO}$	(-) $50$	V
Collector to Emitter Voltage	$V_{CEO}$	(-) $50$	V
Emitter to Base Voltage	$V_{EBO}$	(-) $5$	V
Collector Current	$I_C$	(-) $100$	mA
Collector Current (Pulse)	$I_{CP}$	(-) $200$	mA
Collector Dissipation	$P_C$	$300$	mW
Junction Temperature	$T_j$	$150$	$^\circ C$
Storage Temperature	$T_{stg}$	$-55$ to $+150$	$^\circ C$

**Electrical Characteristics at  $T_a = 25^\circ C$**

		min	typ	max	unit
Collector Cutoff Current	$I_{CBO}$ $V_{CB} = (-)40V, I_E = 0$			(-) $0.1$	$\mu A$
Emitter Cutoff Current	$I_{EBO}$ $V_{EB} = (-)5V, I_C = 0$			(-) $0.1$	$\mu A$
DC Current Gain	$h_{FE}$ $V_{CE} = (-)5V, I_C = (-)10mA$	$100$			
Gain-Bandwidth Product	$f_T$ $V_{CE} = (-)10V, I_C = (-)5mA$		$250$ ( $200$ )		MHz
Output Capacitance	$c_{ob}$ $V_{CB} = (-)10V, f = 1MHz$		$3.7$ ( $5.5$ )		pF
C-E Saturation Voltage	$V_{CE(sat)}$ $I_C = (-)10mA, I_B = (-)0.5mA$			(-) $0.1$ (-) $0.3$	V
C-B Breakdown Voltage	$V_{(BR)CBO}$ $I_C = (-)10\mu A, I_E = 0$		(-) $50$		V
C-E Breakdown Voltage	$V_{(BR)CEO}$ $I_C = (-)100\mu A, R_{BE} = \infty$		(-) $50$		V
Input OFF-State Voltage	$V_{I(off)}$ $V_{CE} = (-)5V, I_C = (-)100\mu A$	(-) $0.4$	(-) $0.55$	(-) $0.8$	V
Input ON-State Voltage	$V_{I(on)}$ $V_{CE} = (-)0.2V, I_C = 10mA$	(-) $0.6$	(-) $0.8$	(-) $1.5$	V
Input Resistance	$R_1$	$1.5$	$2.2$	$2.9$	k $\Omega$

**Electrical Connection**

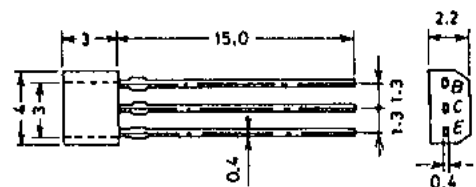


2SA1582(PNP)

2SC4113(NPN)

**Case Outline 2033**

(unit:mm)



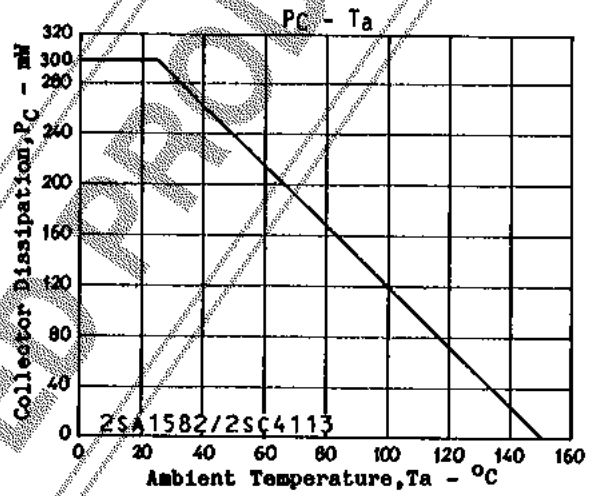
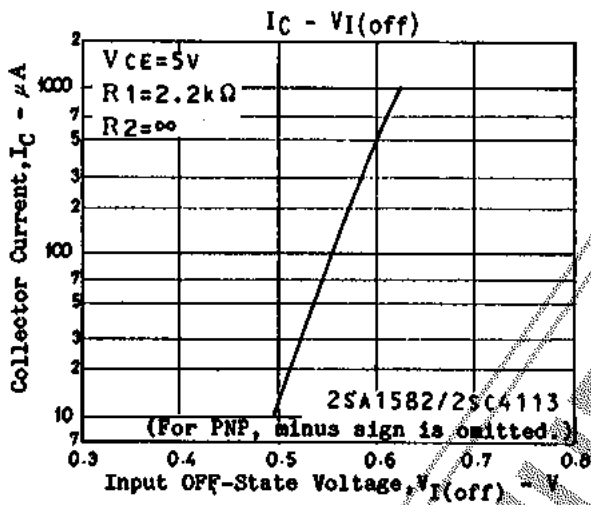
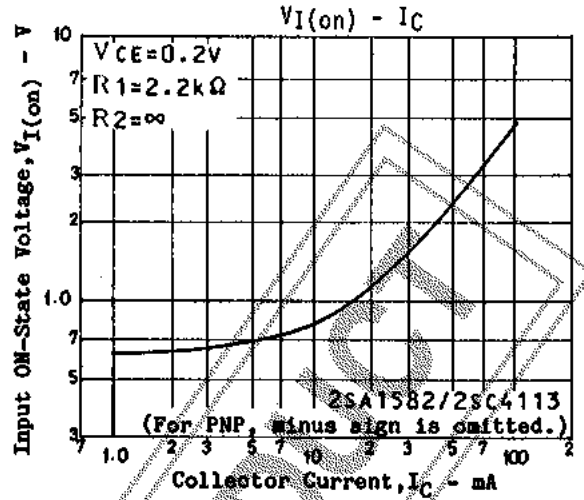
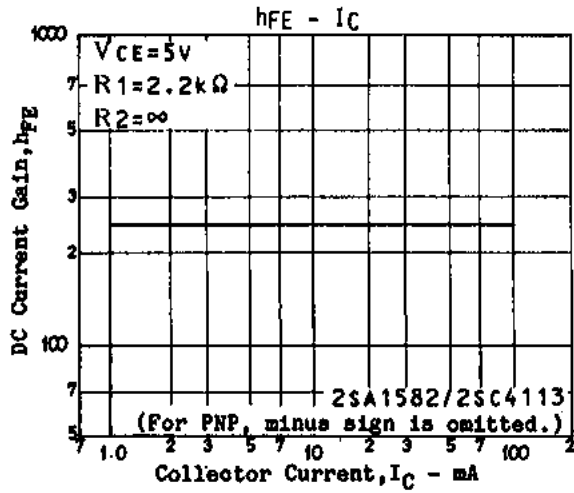
B: Base  
C: Collector  
E: Emitter

SANYO: SPA

Specifications and information herein are subject to change without notice.

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